

Wollongong to Ann Arbor

WolframAlpha™ computational knowledge engine

wollongong to ann arbor

Input Interpretation:
Wollongong, New South Wales, Australia to Ann Arbor, Michigan

Distance:
9477 miles Show metric units



Fraction of Earth circumference:
 $0.38 \approx 1/3$

Direct travel times:

aircraft (550 mph)	17 hours 10 minutes
sound	12 hours 30 minutes
light in fiber	71.3 ms (milliseconds)
light in vacuum	50.9 ms (milliseconds)

(assuming constant-speed great-circle path)

Presentation scheduled start time:

Ann Arbor 11 am EDT, Thursday, July 15, 2010

Wollongong 1 am EST, Friday, July 16, 2010



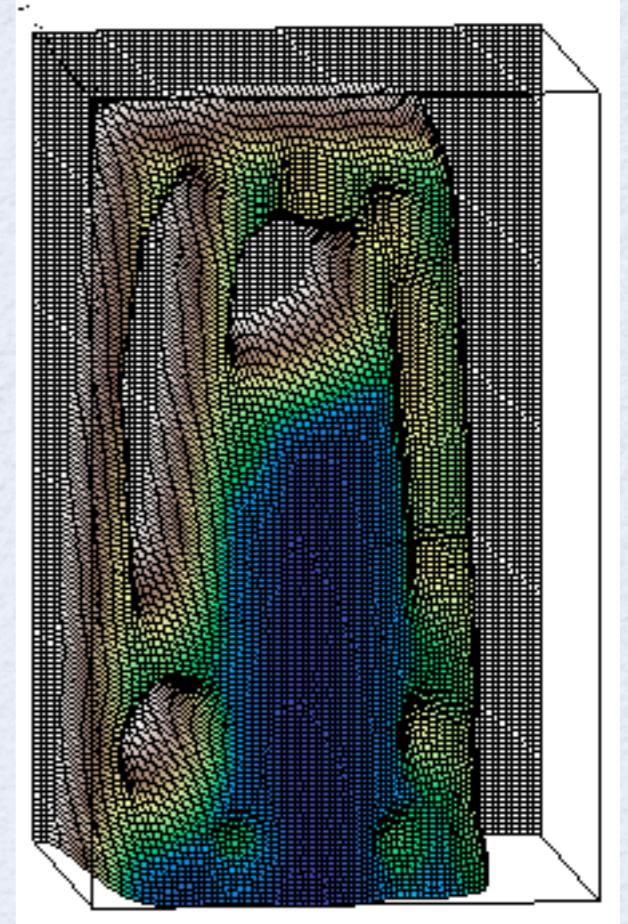
The nature of terahertz emission from GaAsBi

Roger Lewis

*Institute for Superconducting and Electronic Materials,
University of Wollongong, Australia*

THz: seeing the unseen

Fluorescent marker pen: lid on

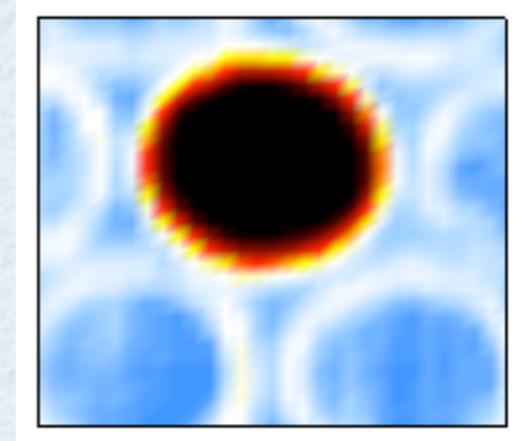


bolo

Cameron Lee
2009

THz: seeing the unseen

Bubble wrap: one bubble with water

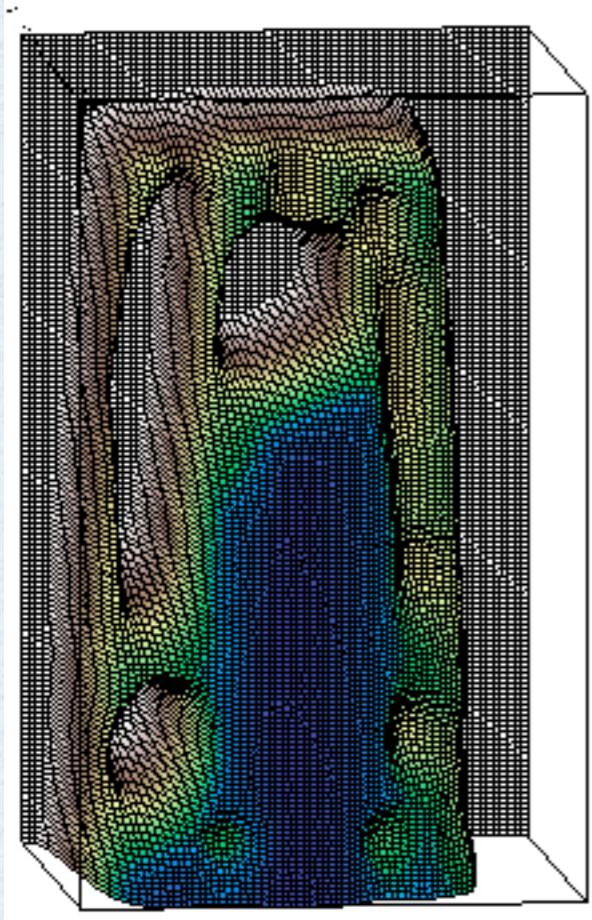


pyro

Cameron Lee
2009

THz: seeing the unseen

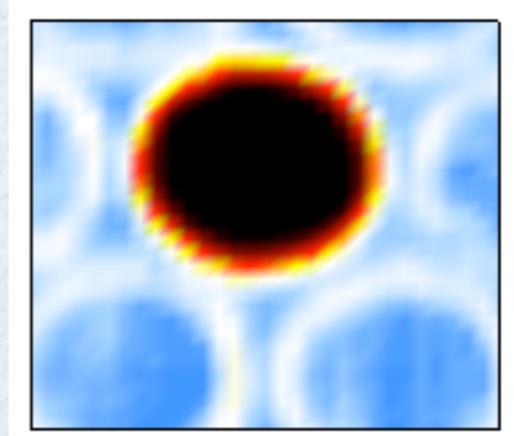
invisible



Eye does not see
through lid

invisible

Eye sees
through water



700 nm

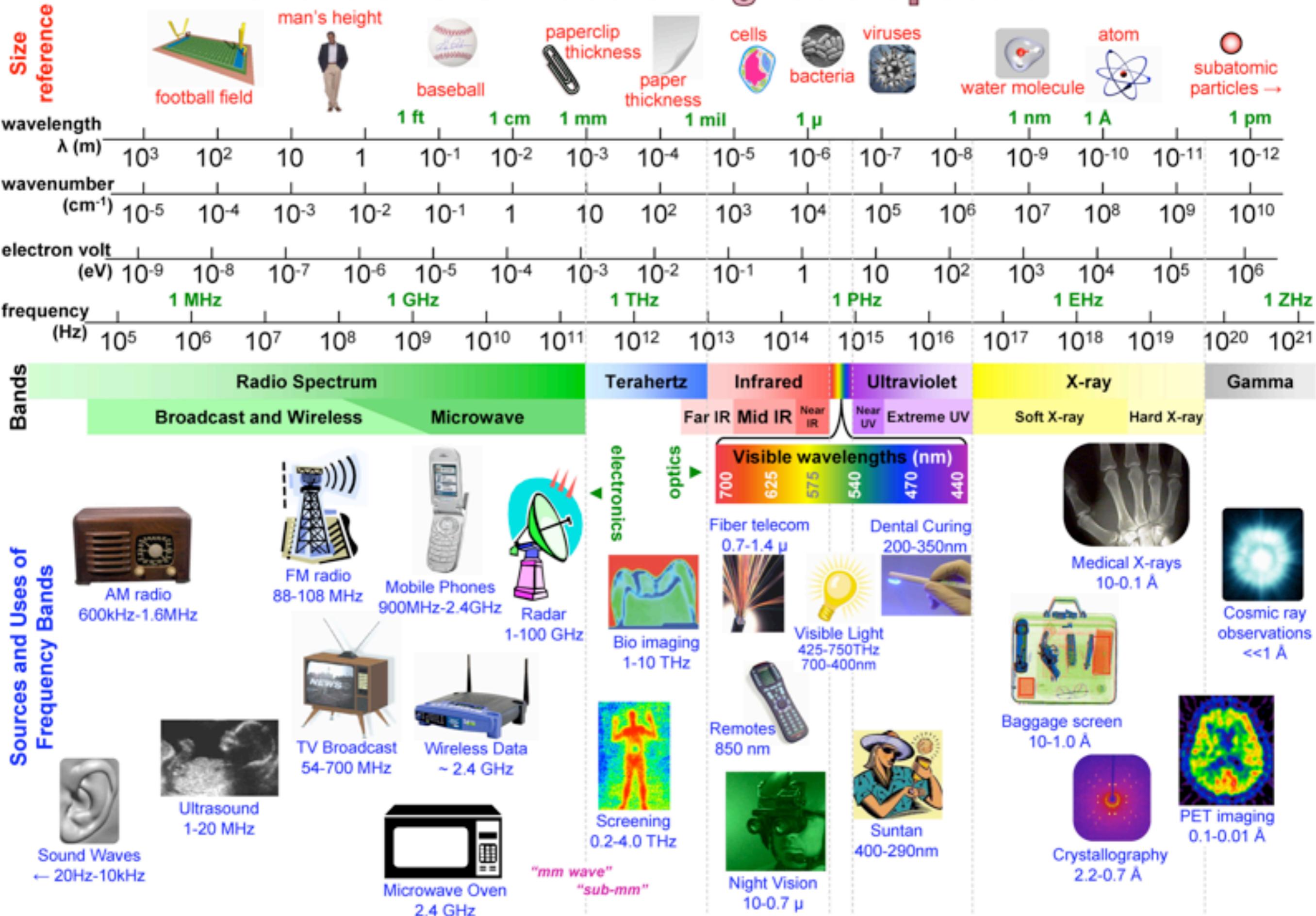
428 THz



400 nm

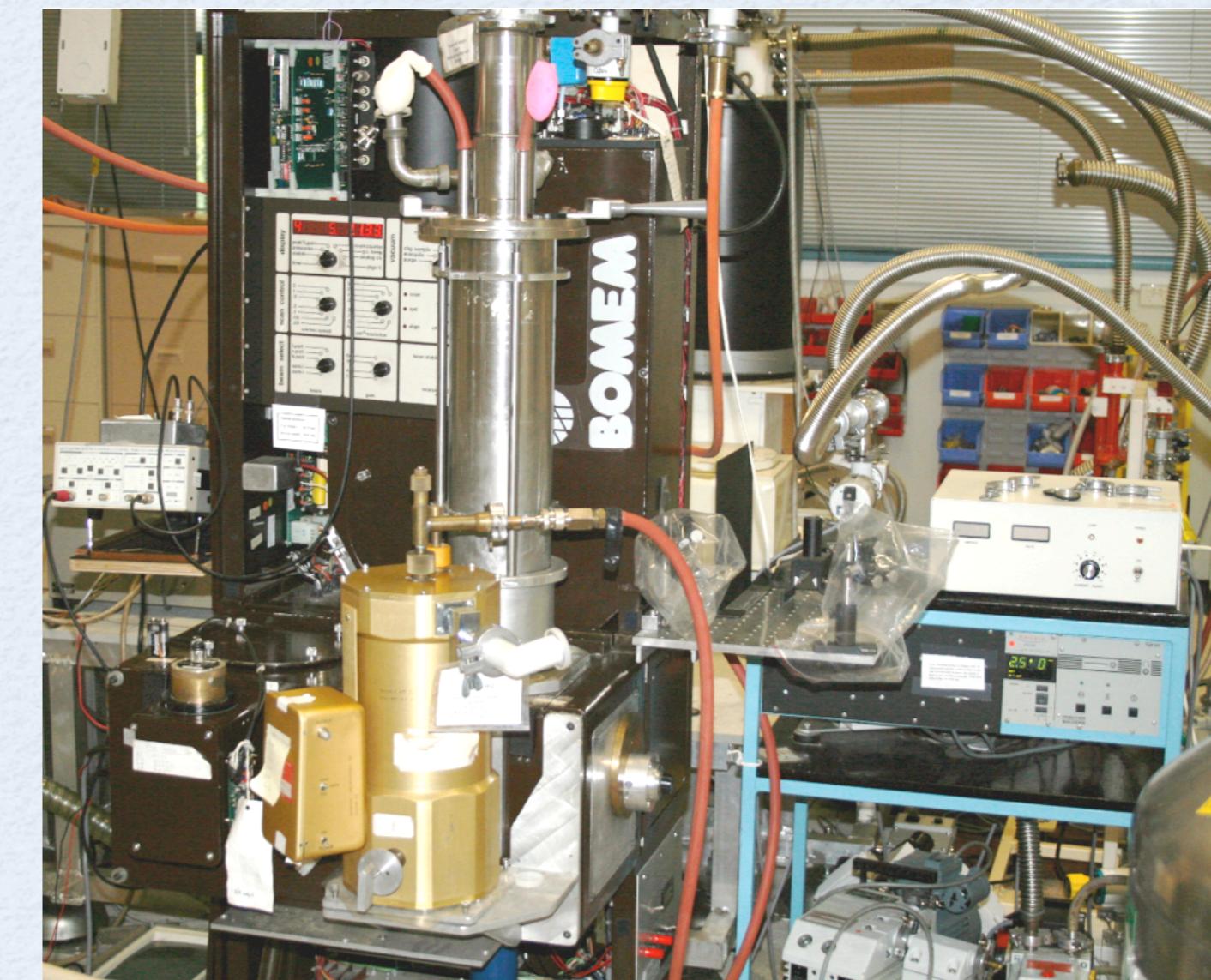
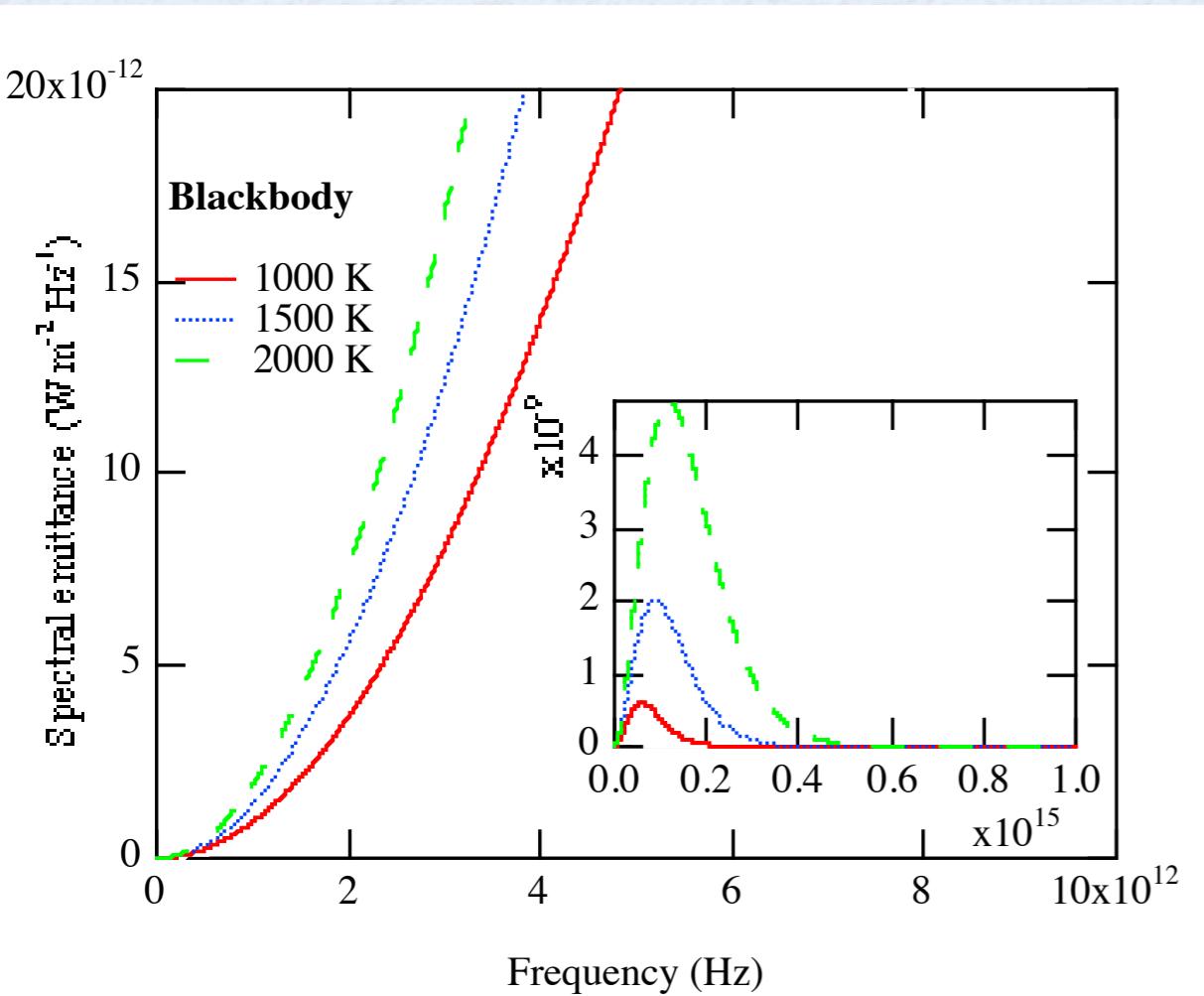
749 THz

Chart of the Electromagnetic Spectrum



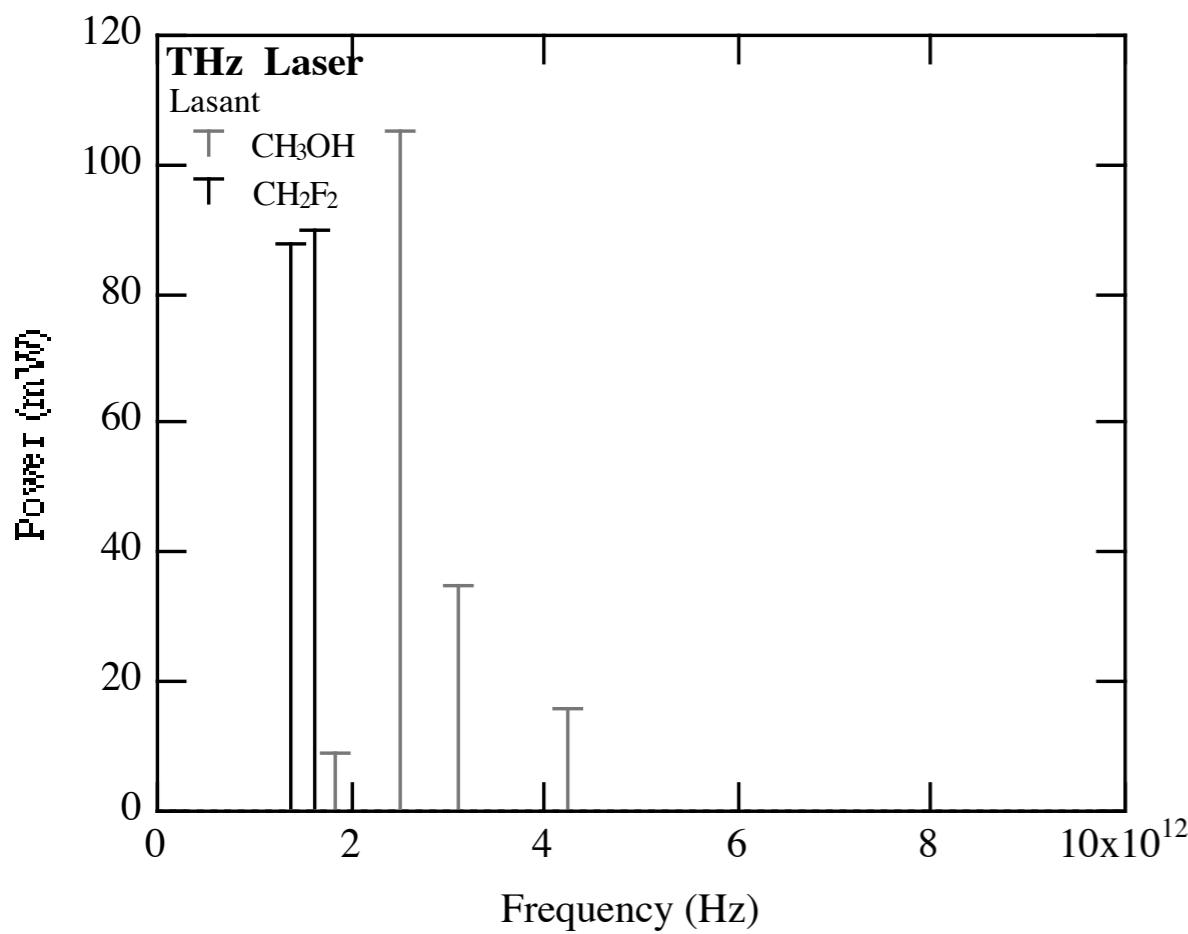
Overview of THz @ UOW; 1 of 4

Blackbody radiation



Overview of THz @ UOW; 2 of 4

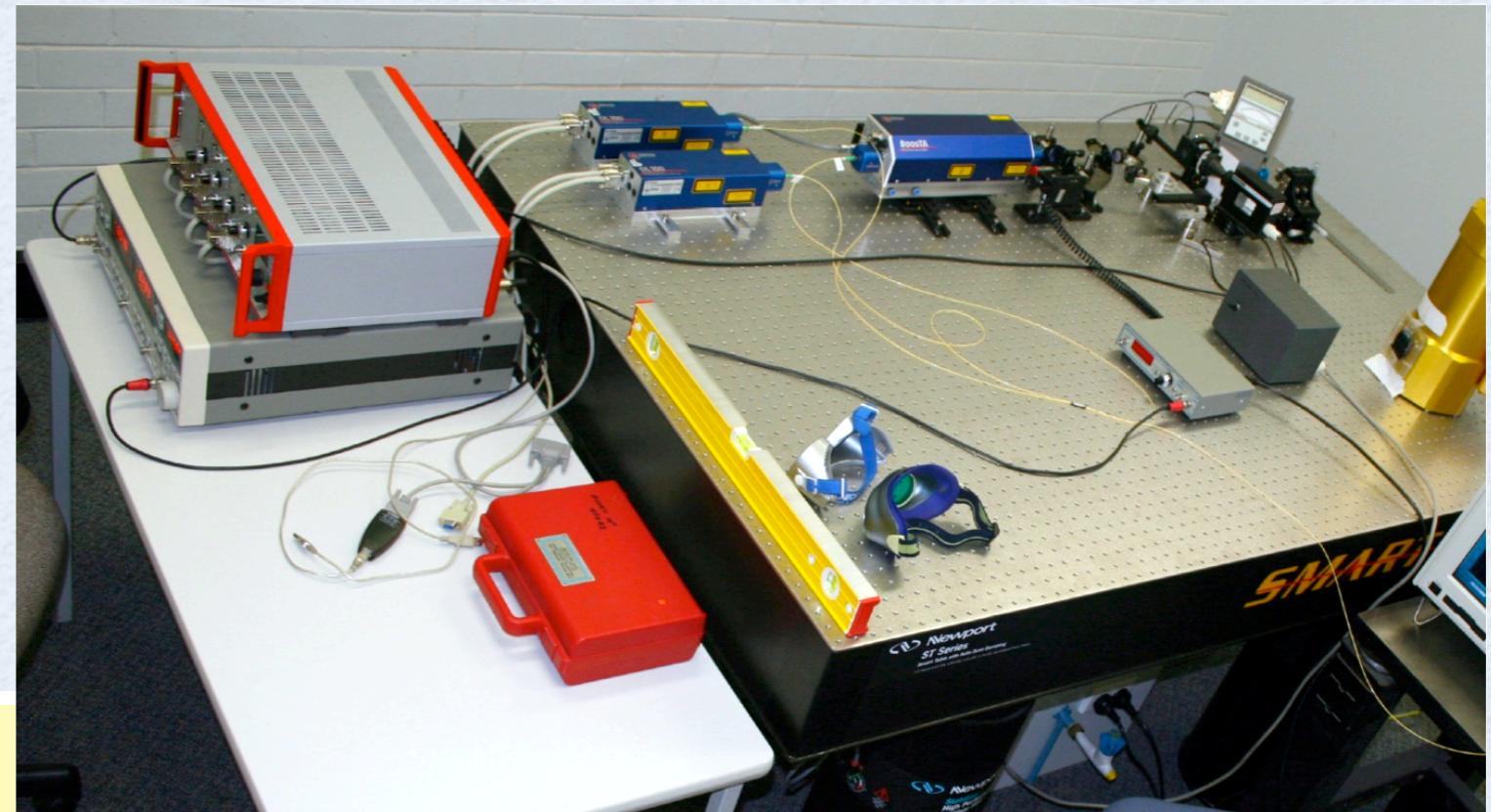
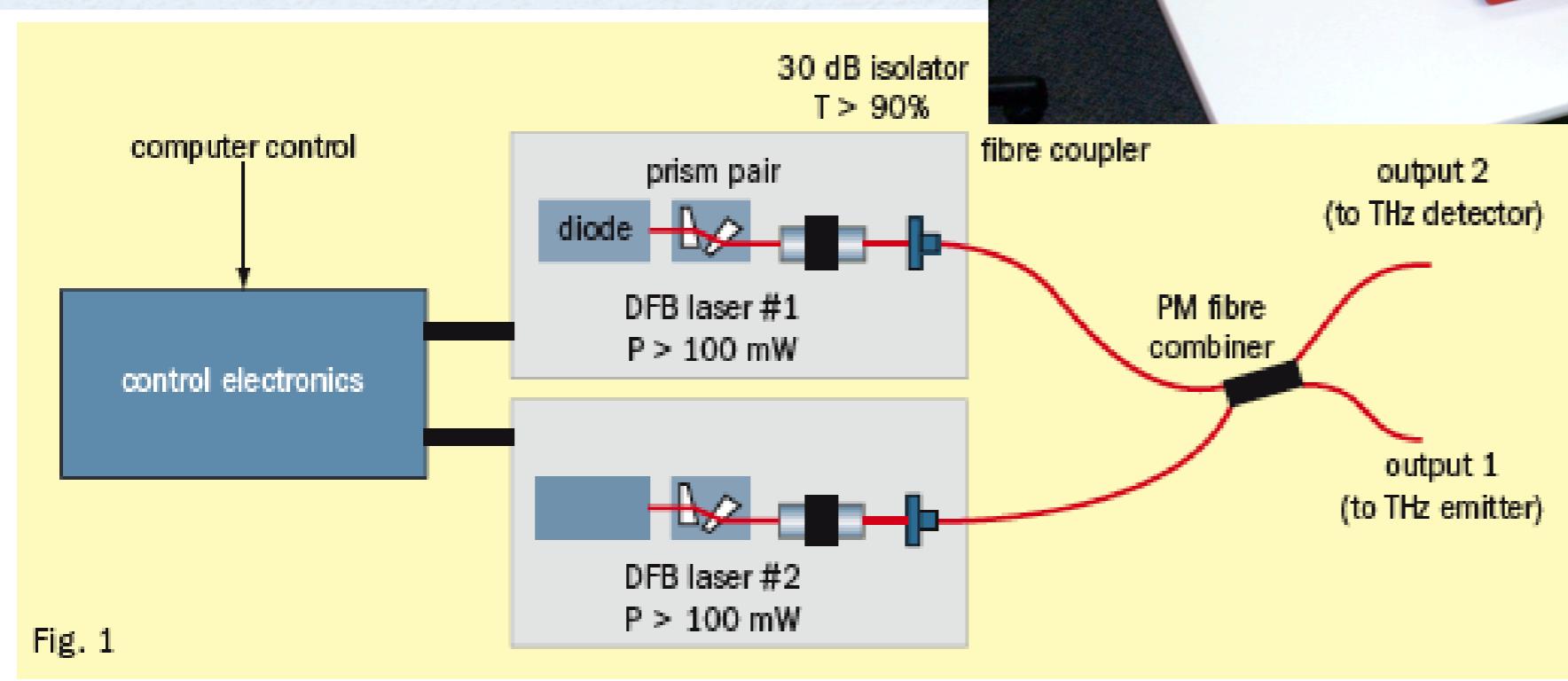
Far-infrared (THz) laser



S. Hargreaves and R. A. Lewis
Journal of Materials Science: Materials in Electronics **18**, S299 (2007)

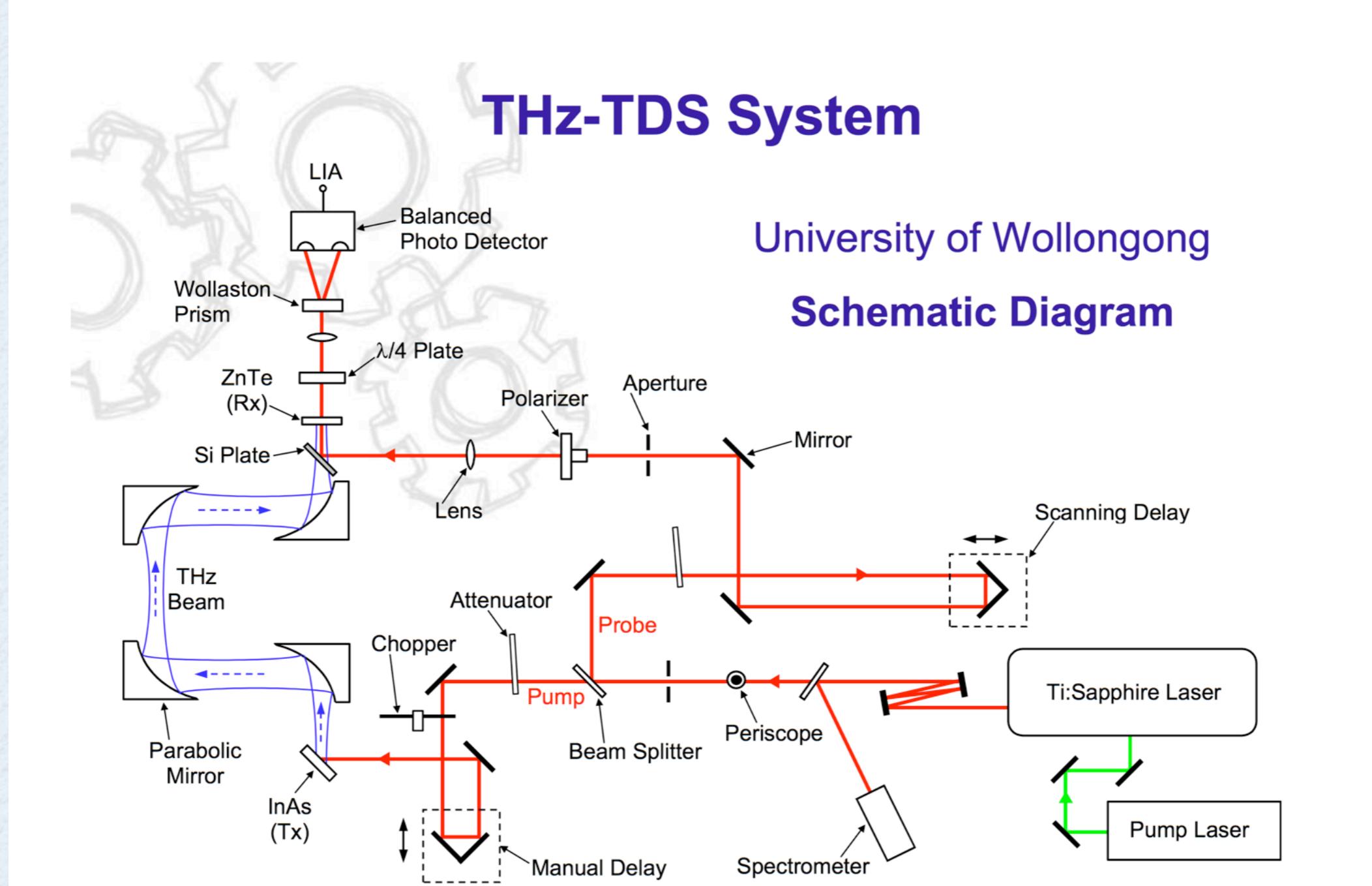
Overview of THz @ UOW; 3 of 4

Two-colour photomixing



Graphic: Toptica

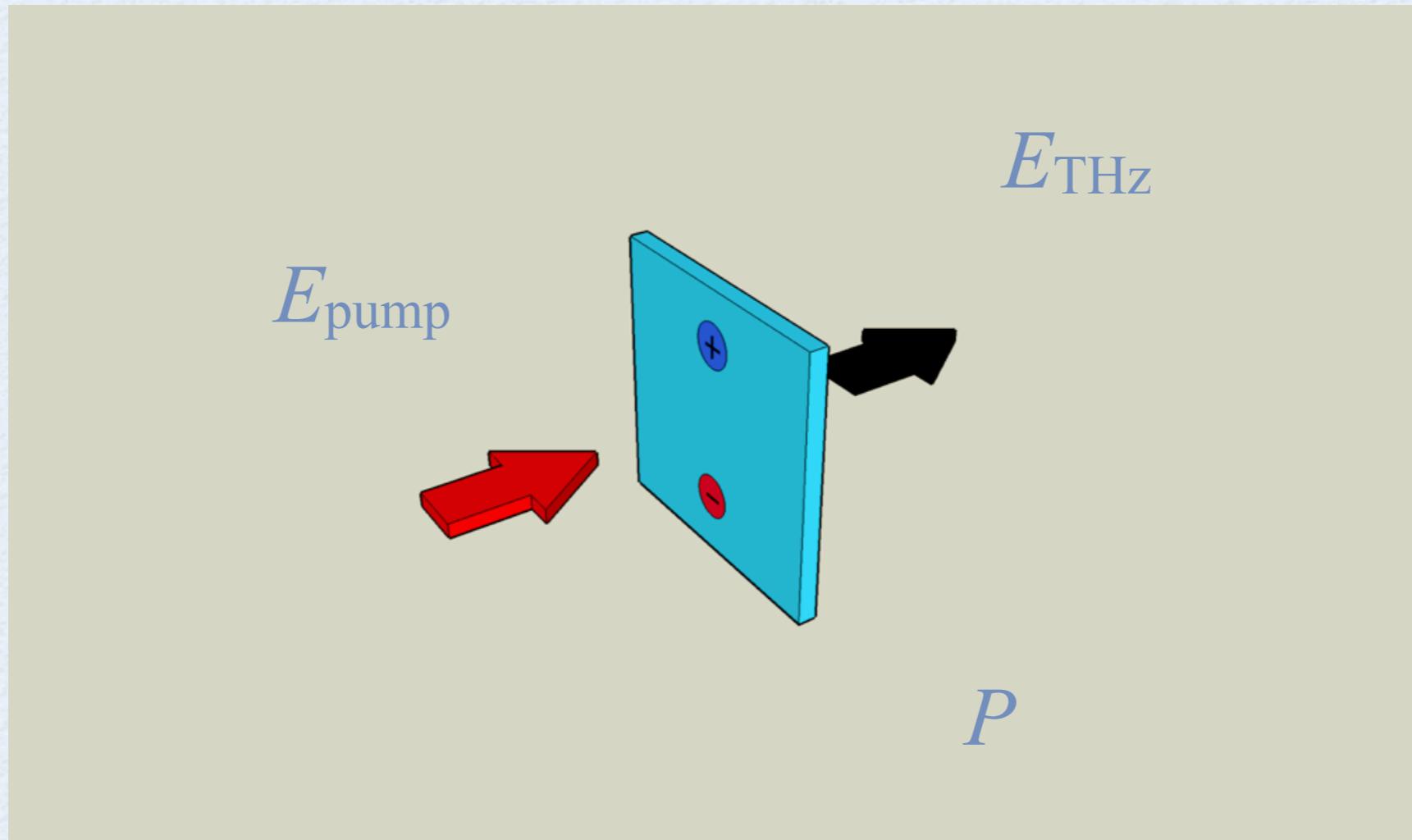
Overview of THz @ UOW; 4 of 4



Graphic: R. Mendis



Ultrashort pulses induce polarization



Graphic: A. Lewis

THz generation by ultrashort pulses

mechanisms

Photoconductivity (PC)

Transient Current (TC)

Optical Rectification (OR)

methods

geometry

polarization

pump-beam power

magnetic field

temperature

bias control



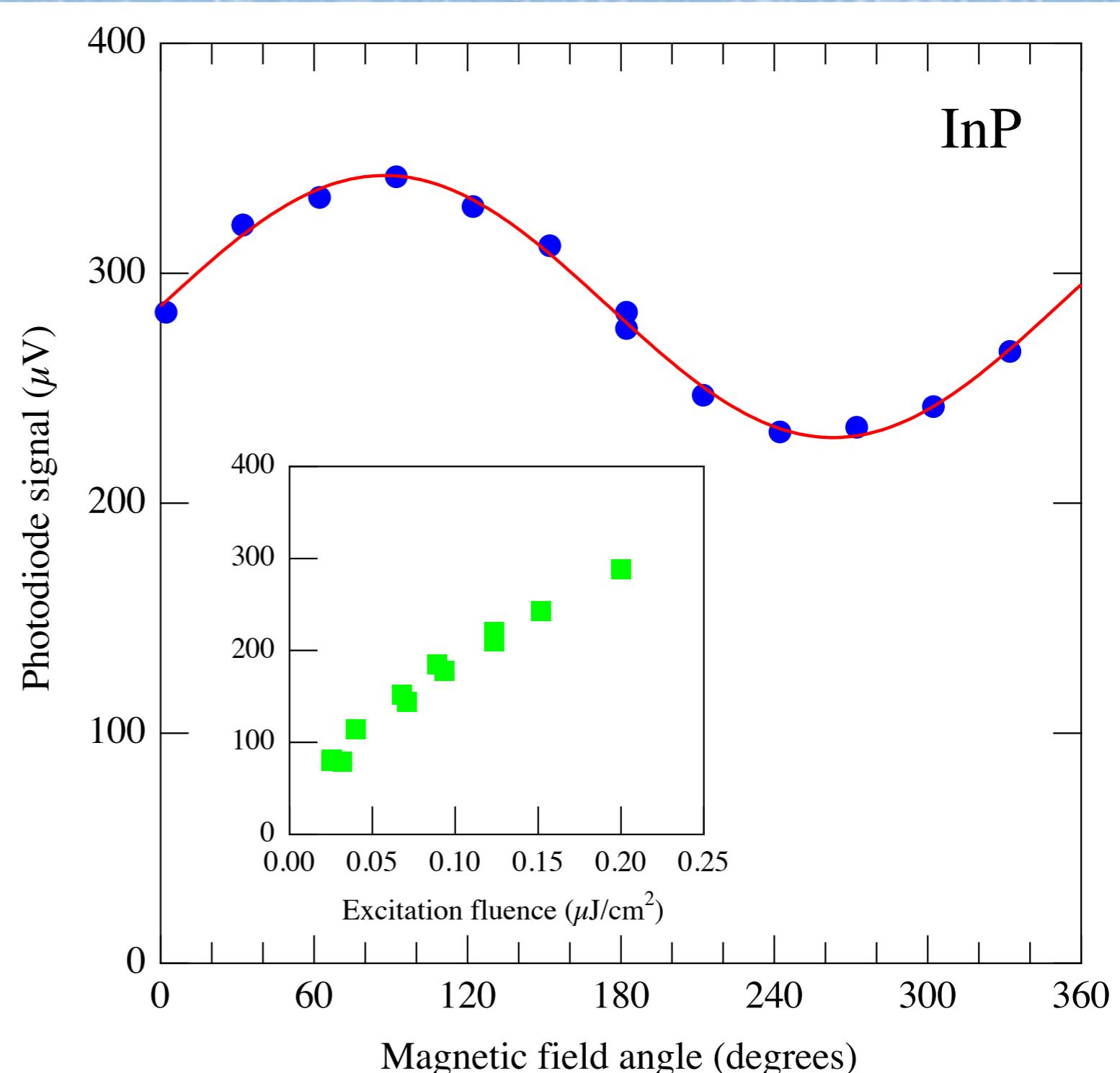
Evidence for Transient Currents

In-plane magnetic field rotates radiating dipole

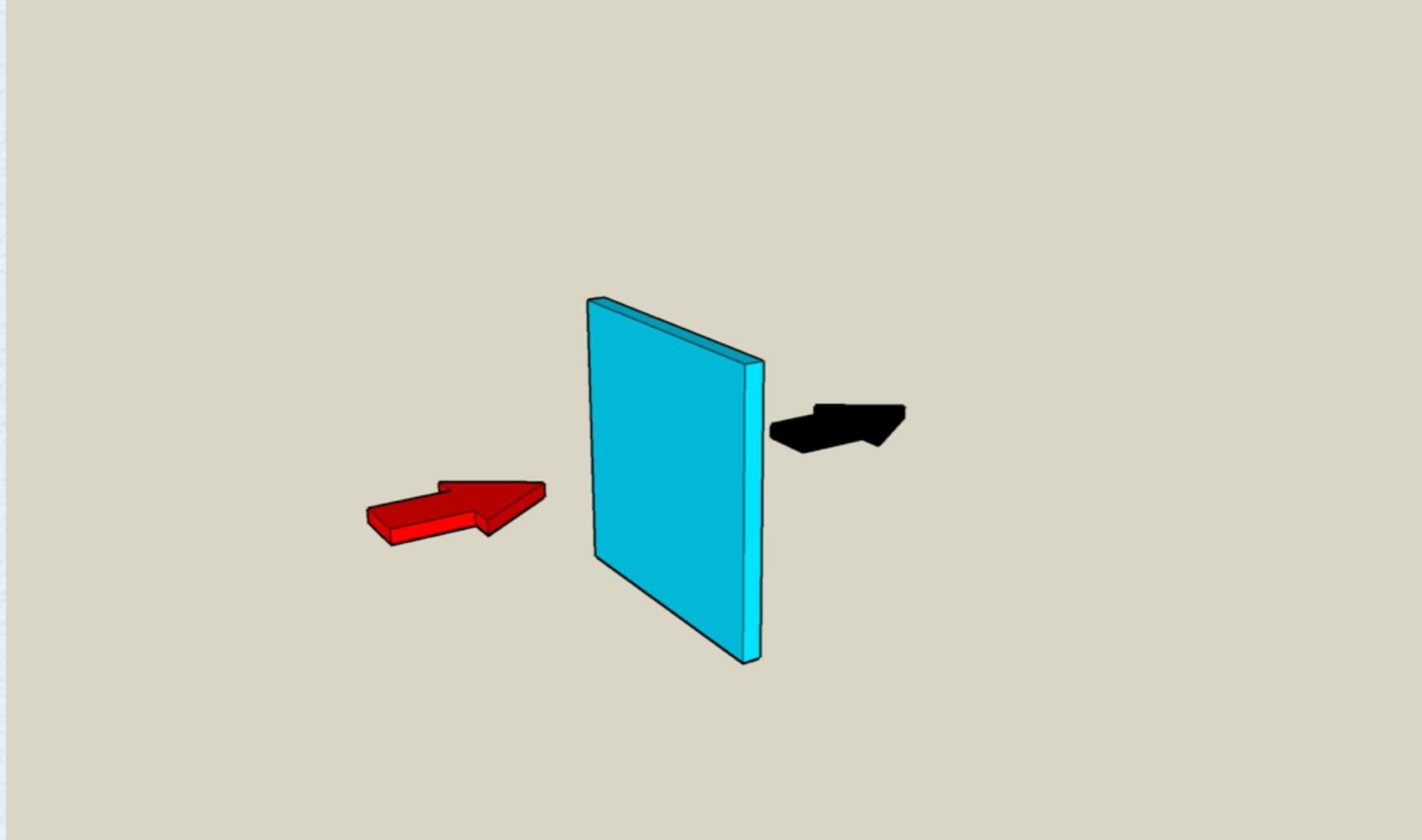
Saturation
with excitation fluence
- carrier screening

FIG. 3. (Color online) Terahertz emission from nominally undoped InP as a function of magnetic field (main figure) and of excitation fluence (inset). The magnetic field is provided by a permanent magnet behind the sample. The magnetic field direction is in the sample plane. The magnetic field angle is measured counterclockwise around the pump beam starting from the incidence-reflection plane. Excitation fluence is $\sim 0.2 \mu\text{J}/\text{cm}^2$. Inset: terahertz emission in the absence of magnetic field as a function of excitation fluence.

S. Hargreaves, R. A. Lewis
Applied Physics Letters
93, 242101 (2008)

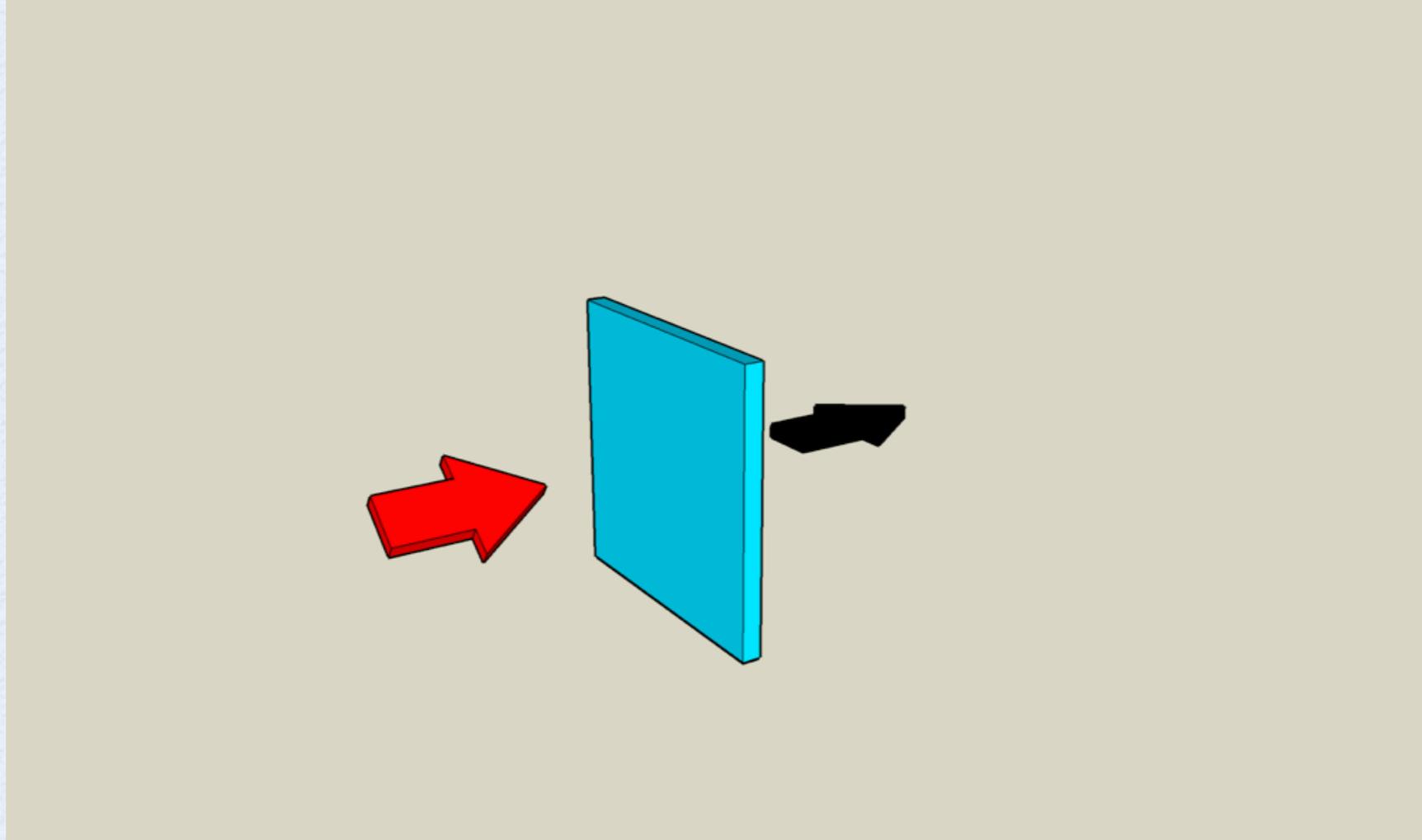


Optical Rectification - geometry



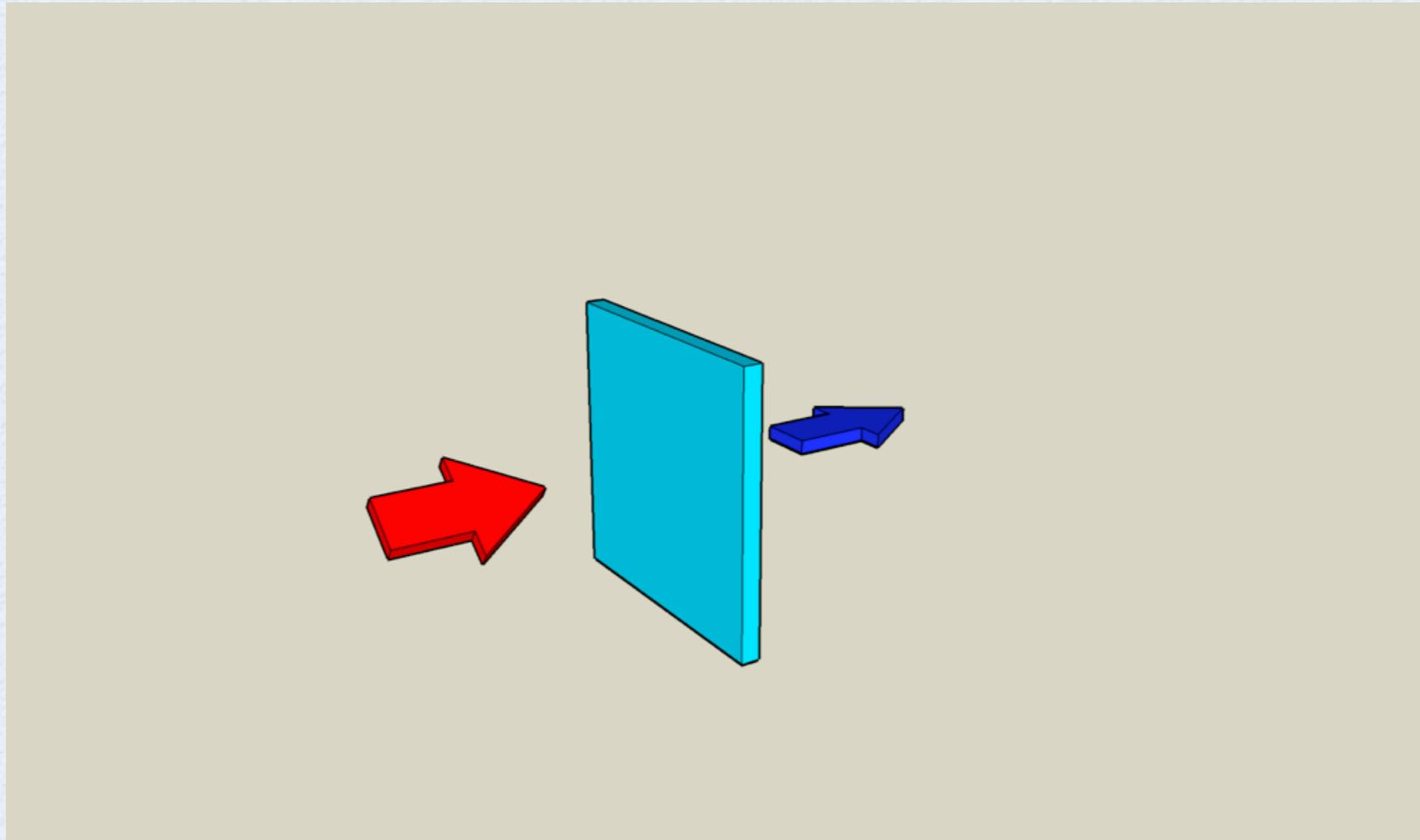
Graphic: A. Lewis

Optical Rectification - geometry



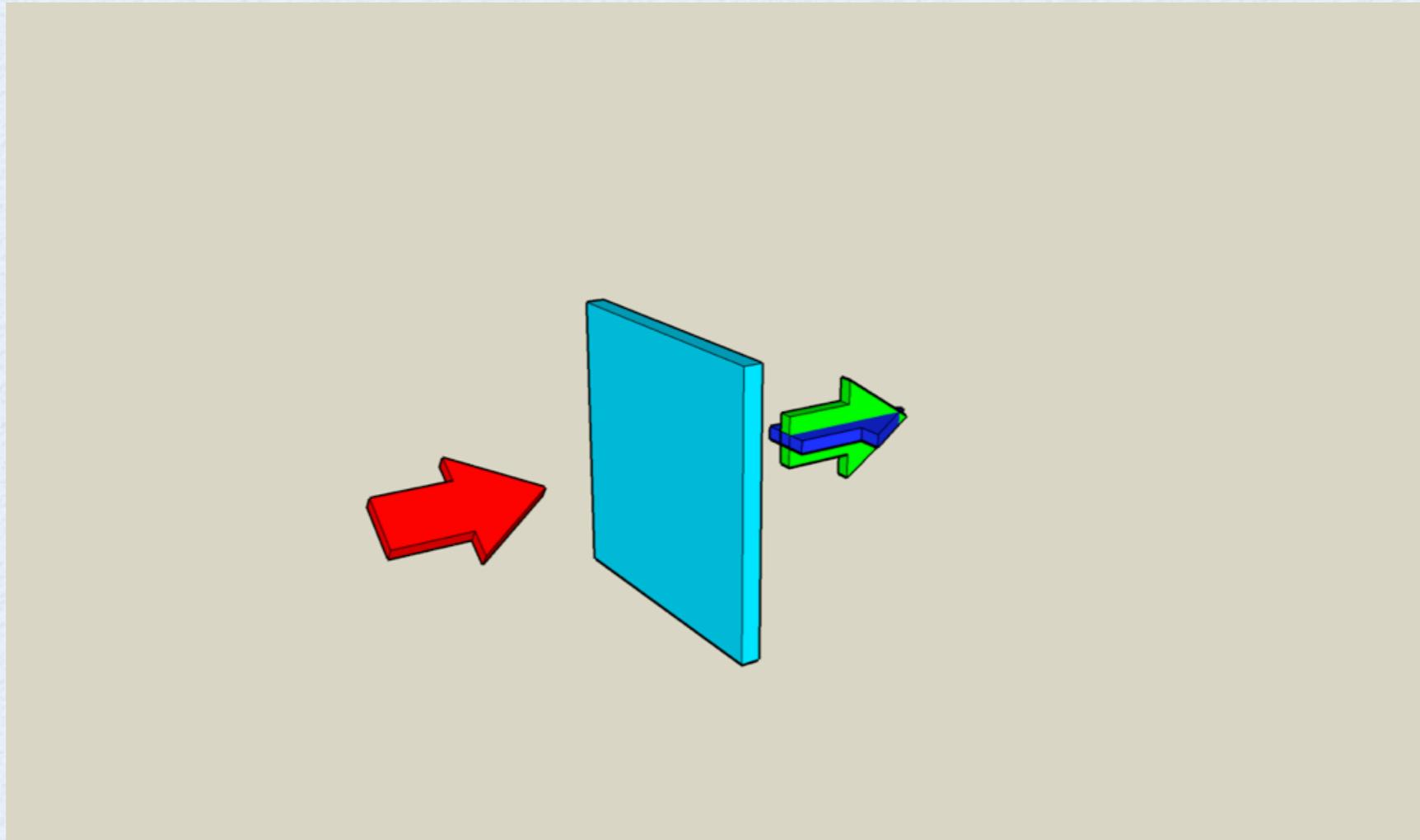
Graphic: A. Lewis

Optical Rectification - geometry



Graphic: A. Lewis

Optical Rectification - geometry



Graphic: A. Lewis

Optical Rectification - geometry

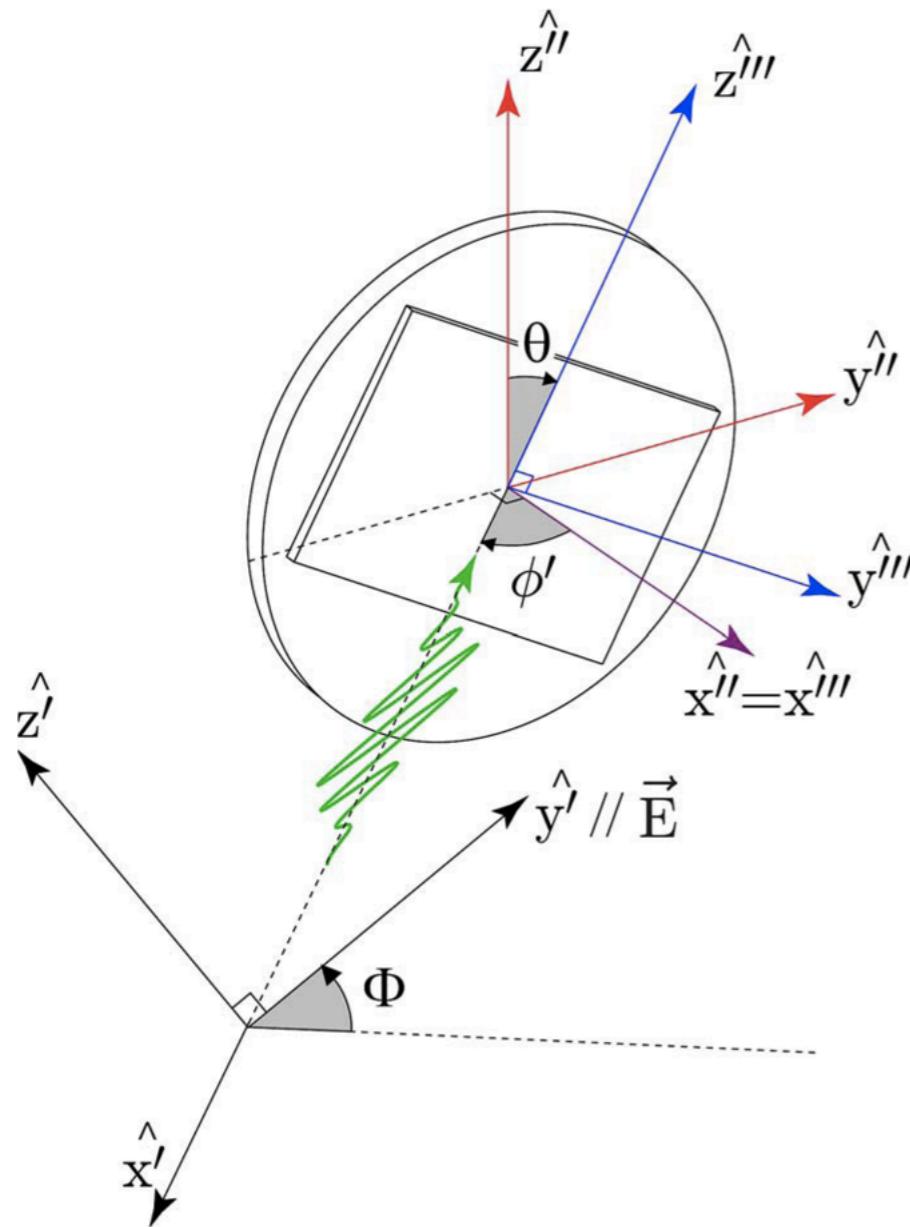


FIG. 1. (Color online) Coordinate axes and angles used. The incident radiation propagates in the $-\hat{x}'$ direction and is polarized in the \hat{y}' direction. The outward-pointing normal to the crystal surface is given by \hat{x}'' . The triple-primed axis system rotates with the crystal. The angle of incidence is ϕ' . The angle of polarization is Φ . The azimuthal angle is θ .

HARGREAVES, RADHANPURA, AND LEWIS
PHYSICAL REVIEW B **80**, 195323 (2009)

Optical Rectification - geometry

$$\begin{bmatrix} P_x''(\text{bulk}) \\ P_y''(\text{bulk}) \\ P_z''(\text{bulk}) \end{bmatrix} = 2 d_{14} E_0^2 \begin{bmatrix} G_{11} & G_{12} & G_{13} & G_{14} & G_{15} & G_{16} & G_{17} \\ G_{21} & G_{22} & G_{23} & G_{24} & G_{25} & G_{26} & G_{27} \\ G_{31} & G_{32} & G_{33} & G_{34} & G_{35} & G_{36} & G_{37} \end{bmatrix} \begin{bmatrix} 1 \\ \cos \theta \\ \sin \theta \\ \cos 2\theta \\ \sin 2\theta \\ \cos 3\theta \\ \sin 3\theta \end{bmatrix}$$

GaAs - Optical Rectification

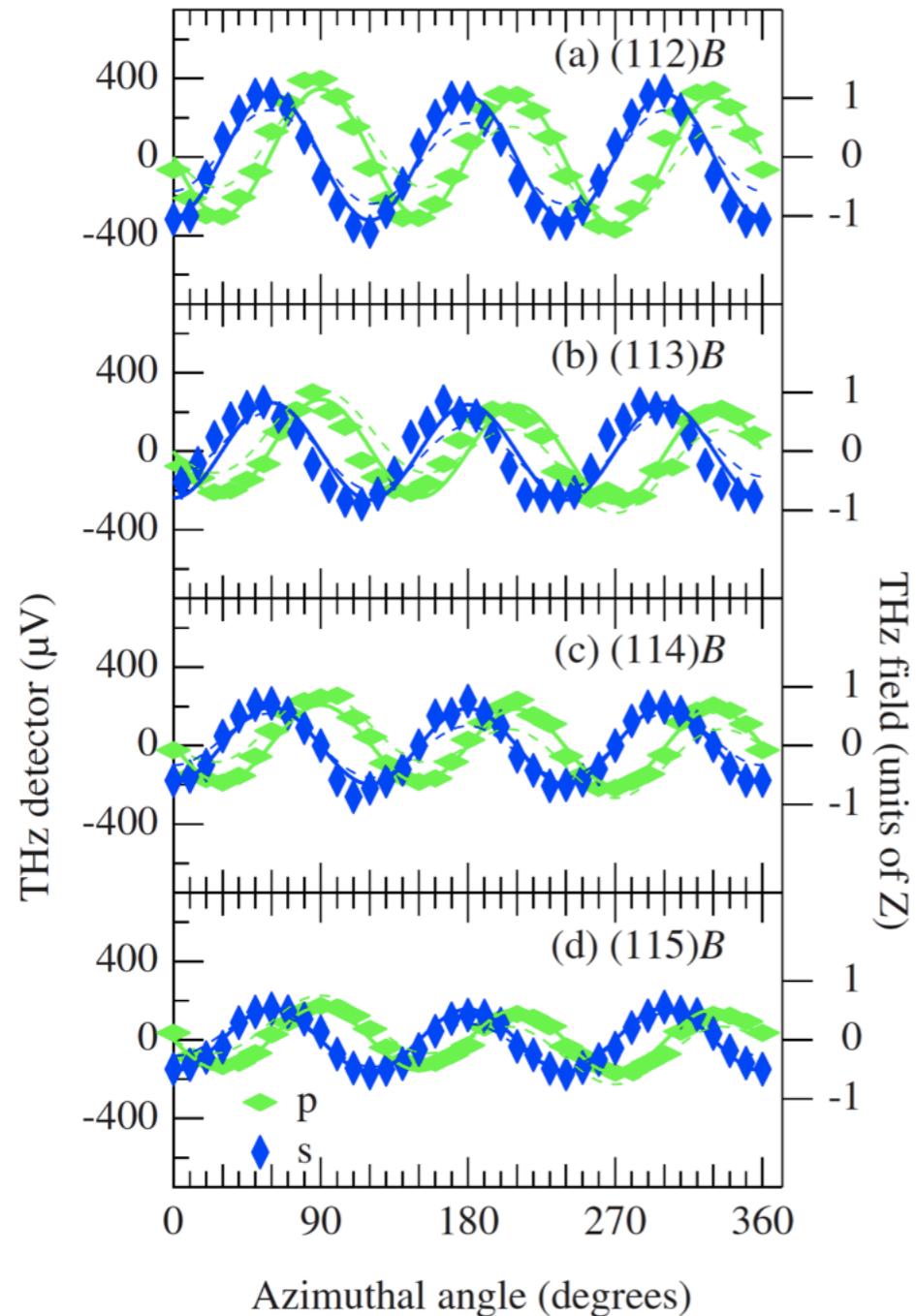


FIG. 3. (Color online) Experimental data (symbols) for THz emission from $(11N)B$ faces of GaAs. The dashed lines are the calculations for bulk optical rectification alone (with $d_{14}E_0^2=1$). The full lines are the calculations for combined bulk ($d_{14}E_0^2=1$) and surface ($\gamma'F_0=1.9d_{14}$) optical rectification.



GaAs - Optical Rectification

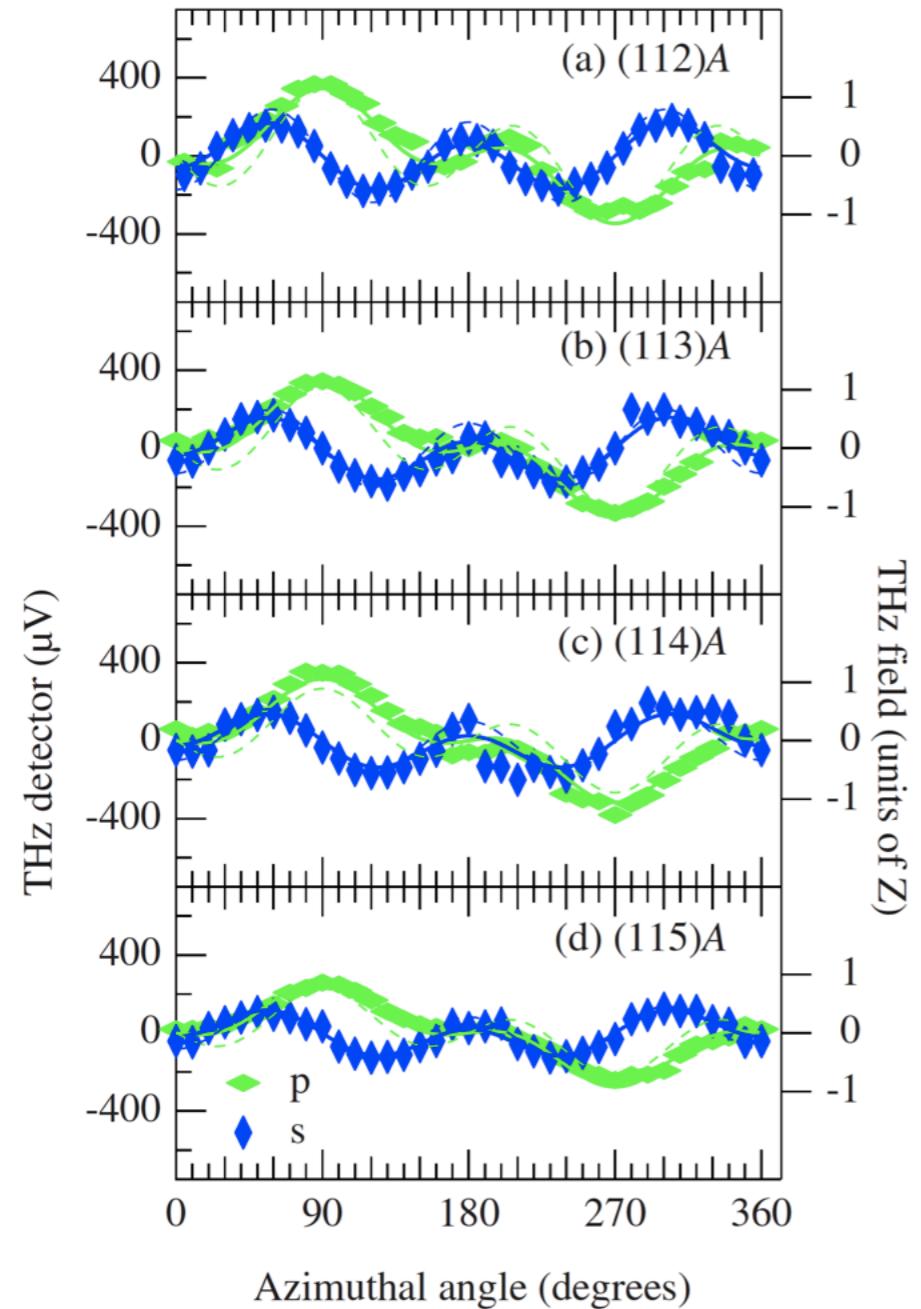


FIG. 4. (Color online) Experimental data (symbols) for THz emission from $(11N)A$ faces of GaAs. The dashed lines are the calculations for bulk optical rectification alone (with $d_{14}E_0^2=1$). The full lines are the calculations for combined bulk ($d_{14}E_0^2=1$) and surface ($\gamma'F_0=-1.6d_{14}$) optical rectification.

GaBiAs

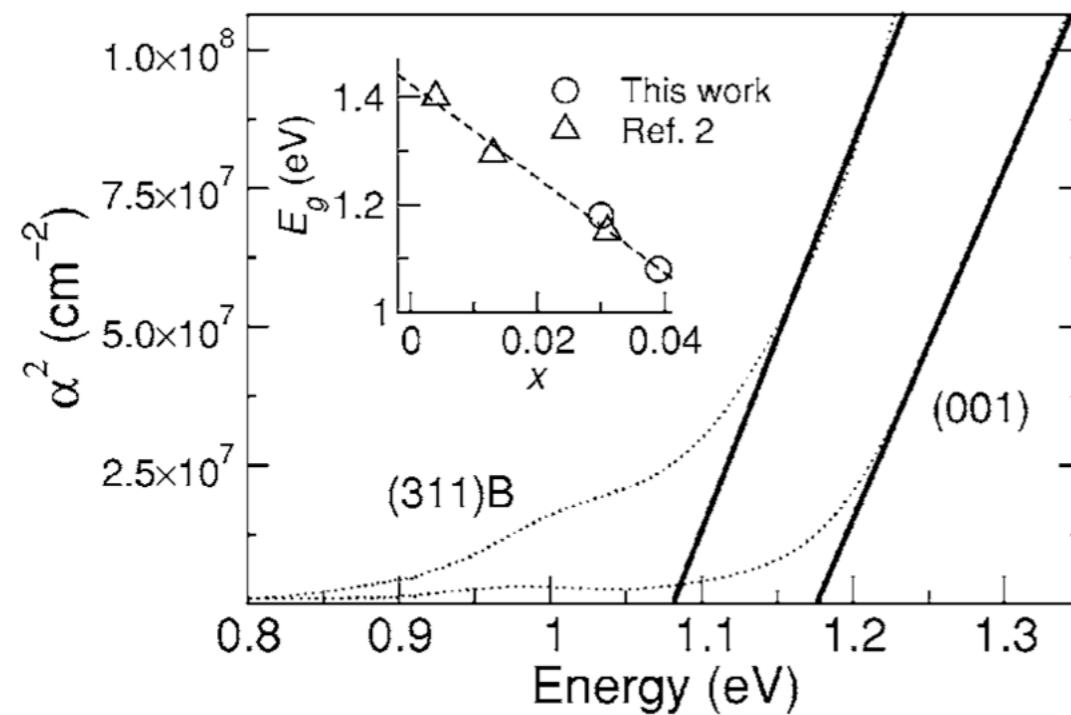


FIG. 3. Square of the absorption coefficient α^2 for the two near-stoichiometric (001) and (311)B $\text{GaBi}_x\text{As}_{1-x}$ epilayers, obtained from transmission measurements at 300 K. Inset: Band-gap energy (E_g) vs x for these two samples, together with data from Ref. 2.

M. Henini *et al.*
Applied Physics Letters
94, 251909 (2007)

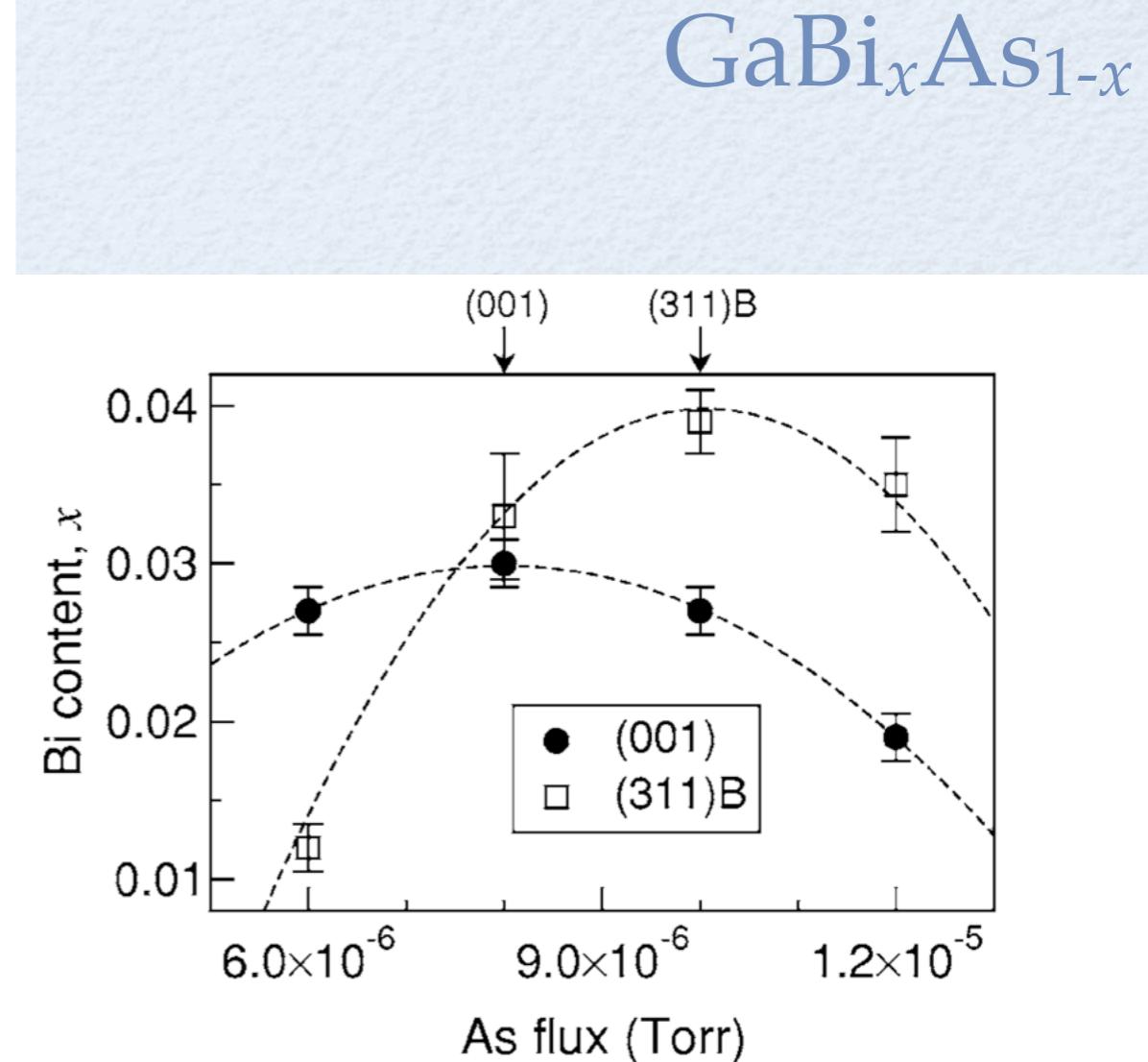


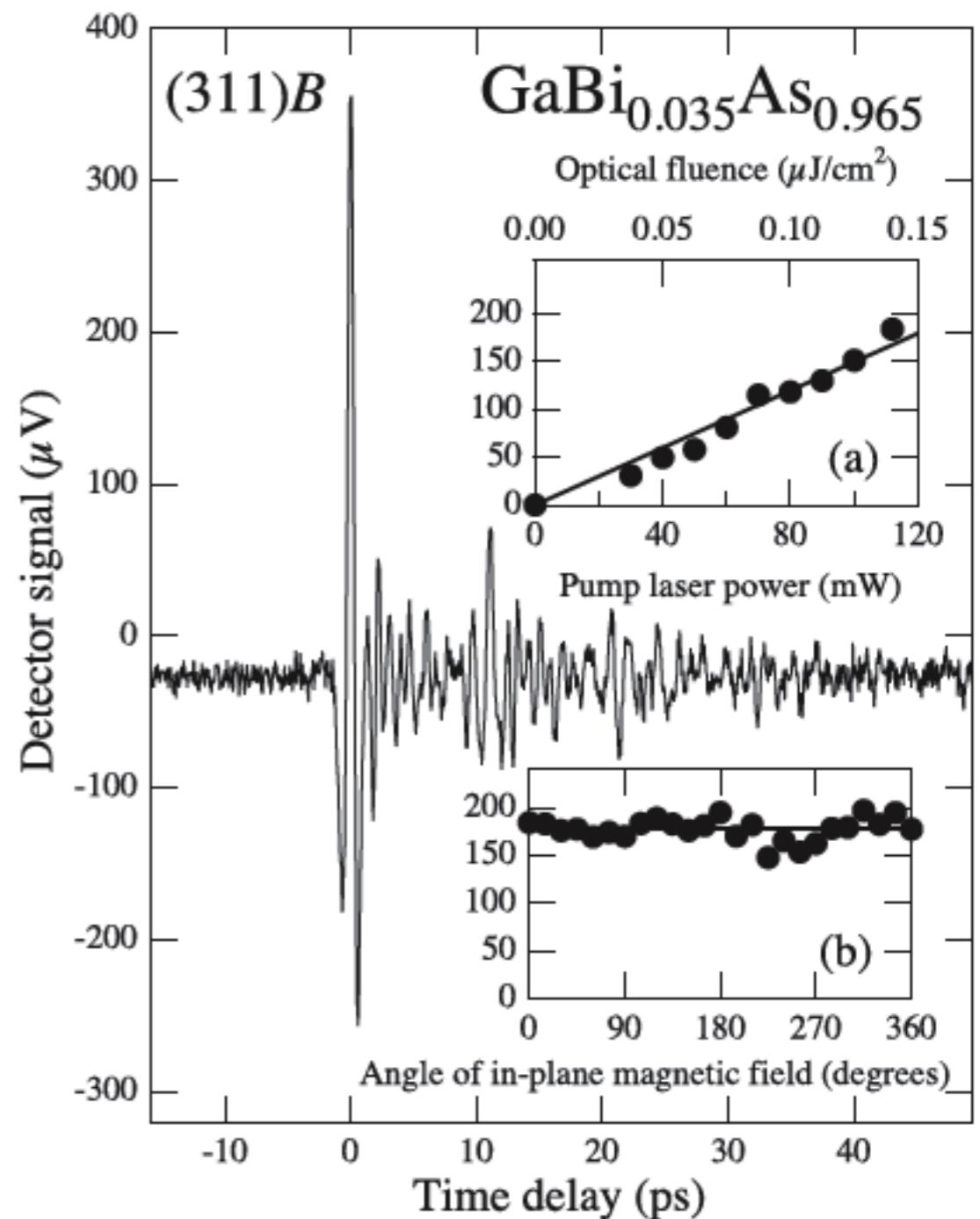
FIG. 2. Bi composition x of different (001) and (311)B $\text{GaBi}_x\text{As}_{1-x}$ epilayers as a function of the As flux used for the growth. The arrows indicate the As flux for near-stoichiometric growth of (001) and (311)B GaAs.

GaBiAs

Not transient currents

FIG. 1. Time-domain spectrum of terahertz field radiated from (311)*B* GaBi_{0.035}As_{0.965} sample (transmission geometry). (a) Dependence of peak terahertz field on optical fluence of pump beam (reflection geometry). (b) Dependence of peak terahertz field on angle of in-plane magnetic field (reflection geometry).

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R. A. Lewis, M. Henini
Applied Physics Letters
94, 251115 (2009)



GaBiAs

Azimuthal angle
dependence
- epilayer
quite different to
substrate

K. Radhanpura, S. Hargreaves,
R. A. Lewis, M. Henini
Applied Physics Letters
94, 251115 (2009)

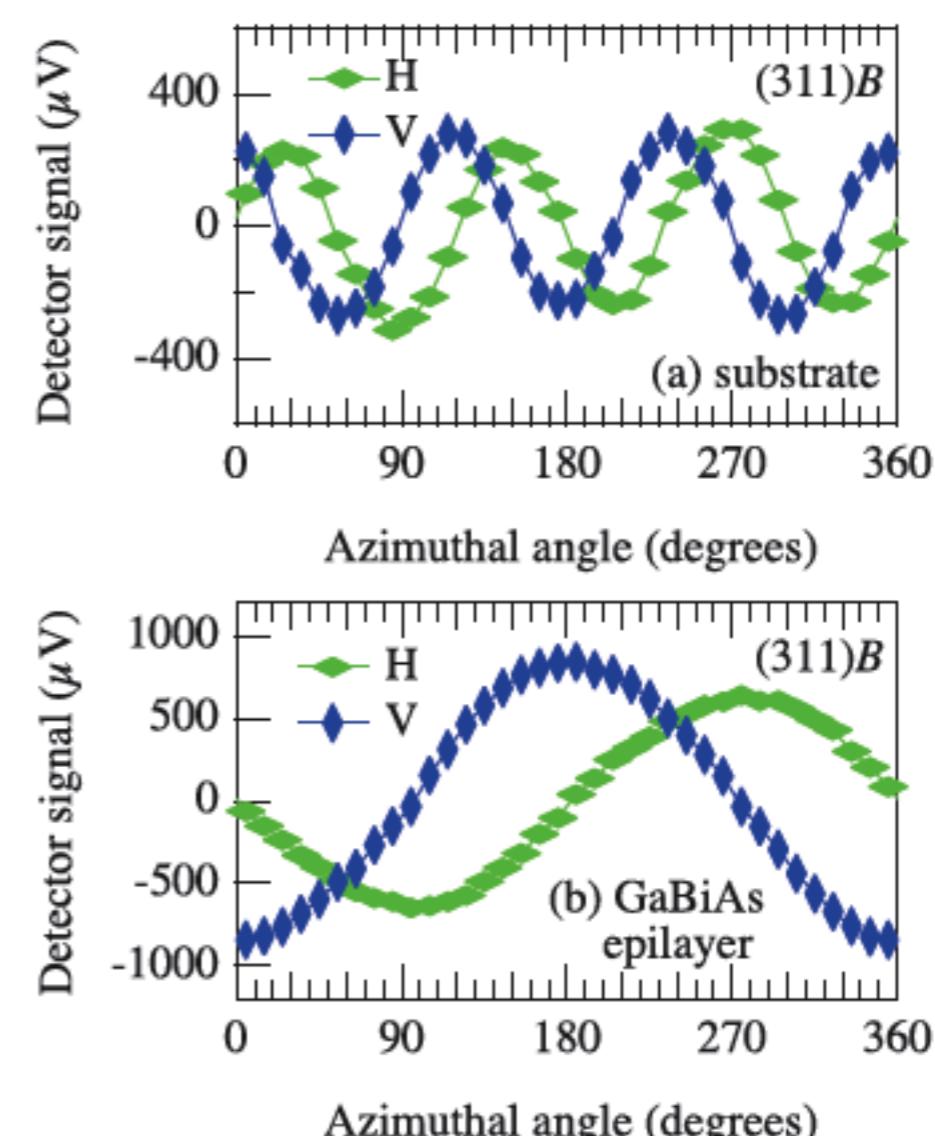


FIG. 2. (Color online) Variation of the peak terahertz field, for both H- and V-polarizations, as a function of angle of rotation around the sample normal in transmission geometry for (311)B (a) substrate and (b) $\text{GaBi}_{0.035}\text{As}_{0.965}$ epilayer.

GaBiAs

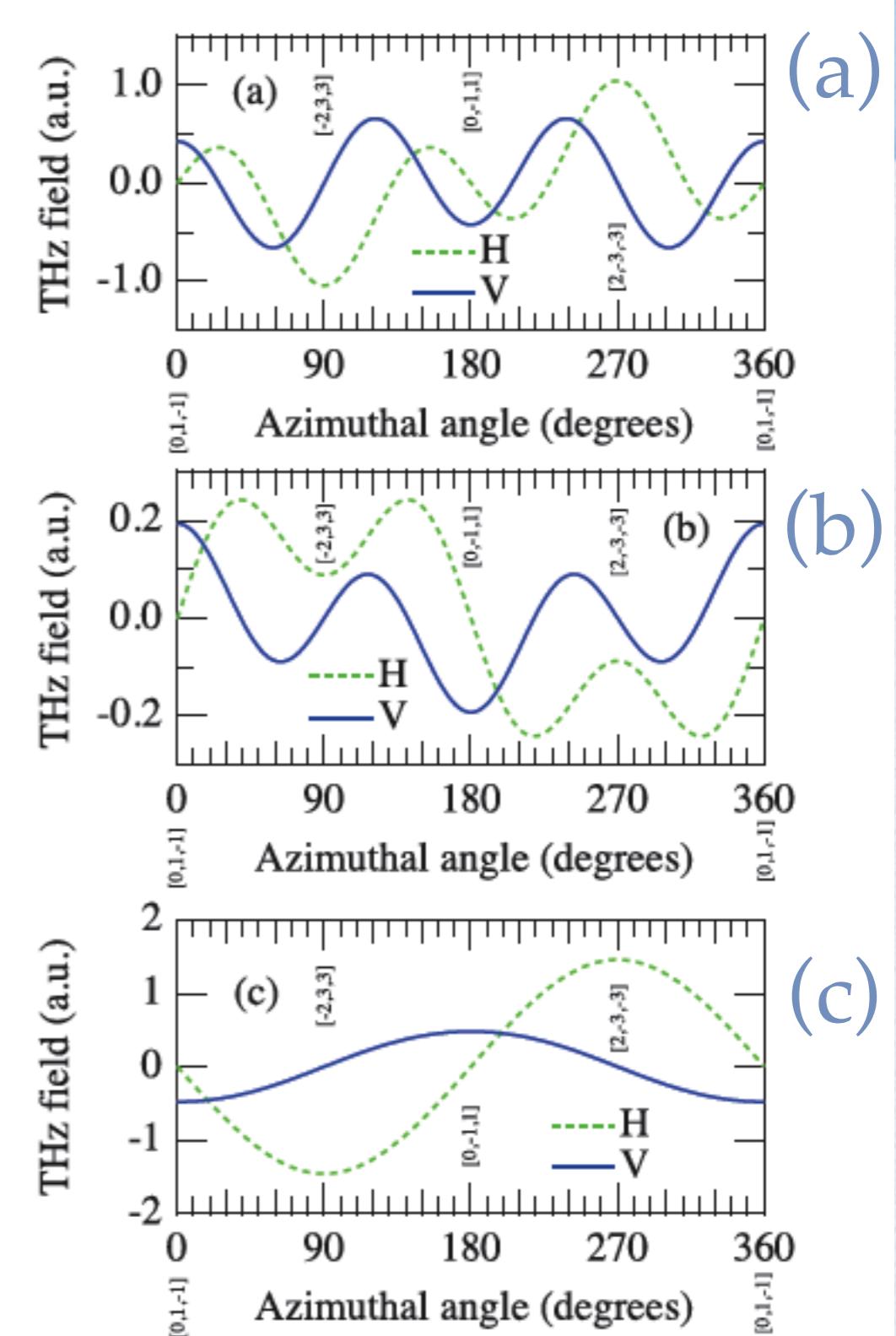
$$P_x = 2d_{14}E_yE_z + \alpha'F_x + \beta'E_x + \gamma'E_x^2F_x, \quad (1)$$

$$P_y = 2d_{14}E_zE_x + \alpha'F_y + \beta'E_y + \gamma'E_y^2F_y, \quad (2)$$

$$P_z = 2d_{14}E_xE_y + \alpha'F_z + \beta'E_z + \gamma'E_z^2F_z. \quad (3)$$

(a) Bulk (b) Surface
(c) Sum of bulk and surface
Optical Rectification

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Applied Physics Letters
94, 251115 (2009)



Conclusion

Optical rectification produces THz radiation

THz field emitted is in general polarized and depends in detail on

- angle of incidence of pump beam
- polarization of pump beam
- index hkl of crystal face
- azimuthal angle of sample relative to pump beam

In GaBiAs the THz radiated depends strongly on

- crystal face hkl
- bulk optical rectification term
- surface field-induced optical rectification term

So THz emission acts as a sensitive surface probe